

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

DECLARATION FOR PATENT APPLICATION

As the below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and joint inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled:

METHOD FOR ETCHING DOPED POLYSILICON WITH HIGH SELECTIVITY TO UNDOPED POLYSILICON.

The specification of which is attached hereto.

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by an amendment, if any, specifically referred to in this oath or declaration.

I acknowledge the duty to disclose all information known to me which is material to patentability as defined in Title 37, Code of Federal Regulations, § 1.56.

I hereby claim foreign priority benefits under Title 35, United States Code, § 119/365 of any foreign application(s) for patent or inventor's certificate listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed:

None

I hereby claim the benefit under Title 35, United States Code, § 120/365 of any United States and PCT international application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code, § 112, I acknowledge the duty to disclose all information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations, § 1.56(a) which became available between the filing date of the prior application and the national or PCT international filing date of this application:

None

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Please address all correspondence to Thomas J. D'Amico of Dickstein Shapiro Morin & Oshinsky LLP located at 2101 L Street, NW, Washington, DC 20037-1526. Telephone calls should be made to Thomas J. D'Amico by dialing (202) 828-2232.

Full name of 1st joint inventor: Garry A. Mercaldi

Inventor's signature  Date 03/31/99

Residence: Meridian, Idaho

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Full name of 2nd joint inventor: Donald L. Yates

Inventor's signature  Date 3/31/99

Residence: Boise, Idaho

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PATENT

Docket No.: M4065.165/P165

Micron No.: 98-0427.00/US

IN THE UNITED STATES
PATENT AND TRADEMARK OFFICE

Patent Application

Inventors: Garry Mercaldi et al.

Serial No.: Not Yet Assigned

Group Art Unit: Not Yet
Assigned

Filed: Concurrently Herewith

Examiner: Not Yet Assigned

For: METHOD FOR ETCHING
DOPED POLYSILICON
WITH HIGH
SELECTIVITY TO
UNDOPED POLYSILICON

POWER OF ATTORNEY BY ASSIGNEE AND

CERTIFICATE BY ASSIGNEE UNDER 37 C.F.R. § 3.73(b)

Micron Technology, Inc., assignee of the entire right,
title and interest in the above-identified application by virtue
of the assignment attached hereto (which is also being submitted
concurrently for recordation), hereby appoints the attorneys and
agents of the firm of Dickstein Shapiro Morin & Oshinsky LLP
located at 2101 L Street, NW, Washington, DC 20037-1526, listed
as follows: Gary M. Hoffman, 26,411; Thomas J. D'Amico, 28,371;
Donald A. Gregory, 28,954; James W. Brady, Jr., 32,115; Jon D.
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39,803; James M. Silbermann, 40,413; Richard Veltman, 36,957; June Cohan, 43,741; and Brian Lemm, 43,748, and also attorneys Michael L. Lynch, 30,871; Lia M. Pappas, 34,095; W. Eric Webostad, 35,406; and Charles B. Brantley, II, 38,086 of Micron Technology, Inc. as its attorneys with full power of substitution to prosecute this application and to transact all business in the Patent and Trademark Office in connection therewith.

The assignee certifies that the above-identified assignment has been reviewed and to the best of the assignee's knowledge and belief, title is in the assignee.

Please direct all correspondence regarding this application to the following:

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MICRON TECHNOLOGY, INC.


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Dated: Jan 31, 1999